

FDP6030BL/FDB6030BL

N-Channel Logic Level PowerTrench® MOSFET

General Description

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

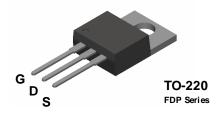
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\scriptscriptstyle DS(\rm cn)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

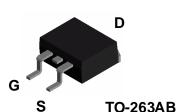
Features

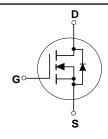
- 40 A, 30 V. $R_{DS(ON)}=0.018~\Omega~@~V_{GS}=10~V$ $R_{DS(ON)}=0.024~\Omega~@~V_{GS}=4.5~V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}.$

FDB Series

• 175°C maximum junction temperature rating.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted

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Symbol	Parameter	FDP6030BL	FDB6030BL	Units						
V _{DSS}	Drain-Source Voltage	;	30	V						
V _{GSS}	Gate-Source Voltage	±	20	V						
I _D	Maximum Drain Current - Continuous (Note 1)	4	10	Α						
	- Pulsed	1	20							
P_D	Total Power Dissipation @ T _C = 25°C	(W							
	Derate above 25°C	0	W/°C							
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-65 to	°C							
Therma	I Characteristics									
$R_{\theta_{JC}}$	Thermal Resistance, Junction-to-Case	2	2.5	°C/W						
RθJA	Thermal Resistance, Junction-to-Ambient	6	2.5	°C/W						

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB6030BL	FDB6030BL	13"	24mm	800
FDP6030BL	FDP6030BL	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RAT	INGS (Note 1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15 \text{ V}, I_D = 40 \text{ A}$			150	mJ
I _{AR}	Maximum Drain-Source Avalnche	Current			40	Α
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
ΔBVdss ΔT,	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μд
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Chara	acteristics (Note 1)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.6	3	V
$\Delta V_{GS(th)} = \Delta T_{J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-4.5		mV/°C
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$		0.015 0.021 0.019	0.018 0.030 0.024	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 10 V	40			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		30		S
Dvnamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		1160		pF
Coss	Output Capacitance	f = 1.0 MHz		250		pF
C _{rss}	Reverse Transfer Capacitance			100		pF
Switchin	q Characteristics (Note 1)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_{D} = 1 \text{ A},$		9	17	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_{GEN} = 6 Ω		11	20	ns
t _{d(off)}	Turn-Off Delay Time			23	37	ns
t _f	Turn-Off Fall Time			8	16	ns
Q_g	Total Gate Charge	V _{DS} = 15 V,		12	17	nC
Q _{gs}	Gate-Source Charge	$I_D = 20 \text{ A}, V_{GS} = 5 \text{ V}$		3.2		nC
Q_{gd}	Gate-Drain Charge			3.7		nC
Drain-So	urce Diode Characteristics	and Maximum Ratings				
l _s	Maximum Continuous Drain-Source				40	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 20 \text{ A}$ (Note 1)		0.95	1.2	V

Note: 1. Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

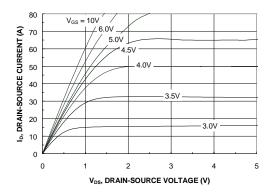


Figure 1. On-Region Characteristics.

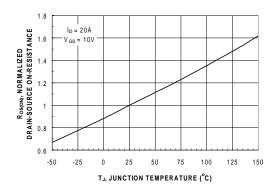


Figure 3. On-Resistance Variation with Temperature.

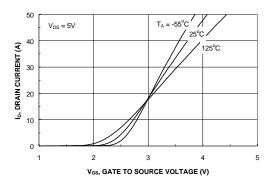


Figure 5. Transfer Characteristics.

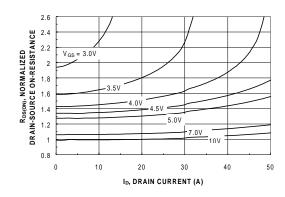


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

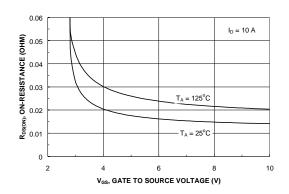


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

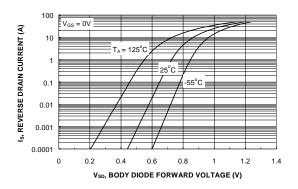
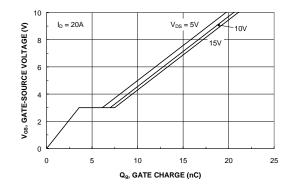


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



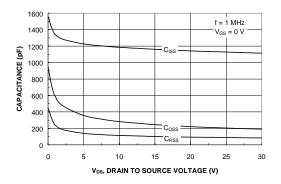
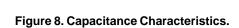
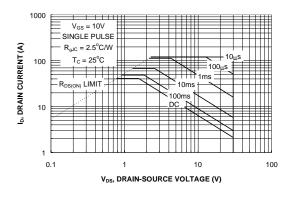


Figure 7. Gate-Charge Characteristics.





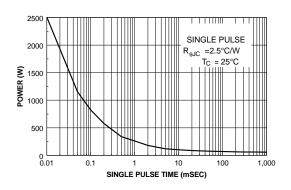


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

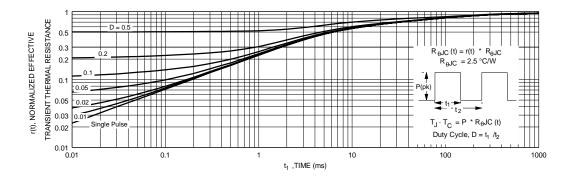
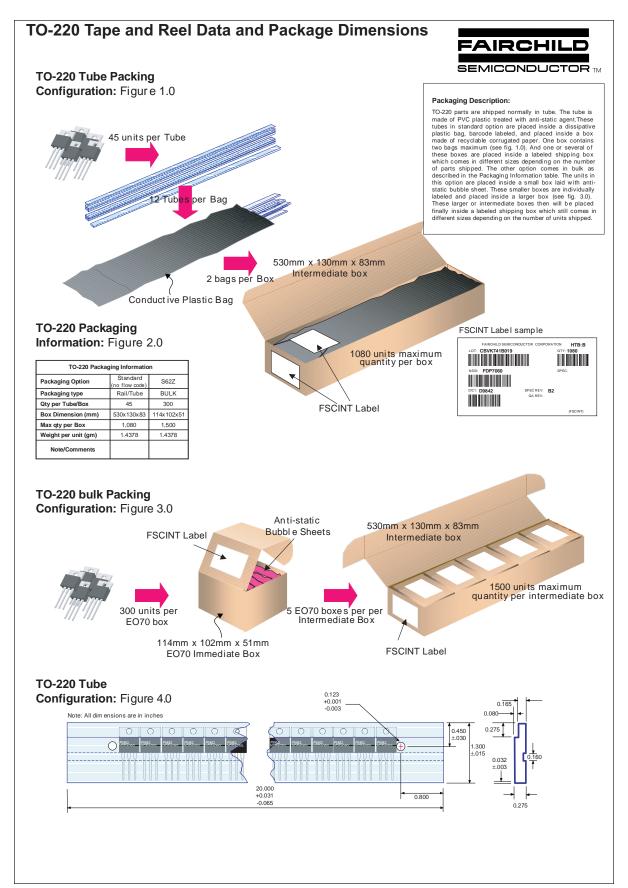
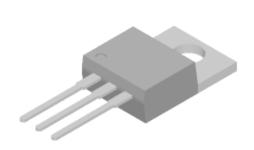


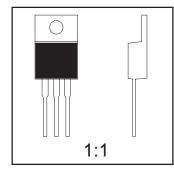
Figure 11. Transient Thermal Response Curve.



TO-220 Tape and Reel Data and Package Dimensions, continued

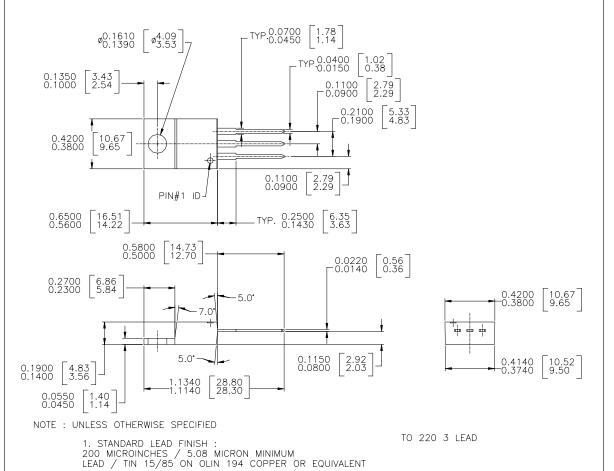
TO-220 (FS PKG Code 37)

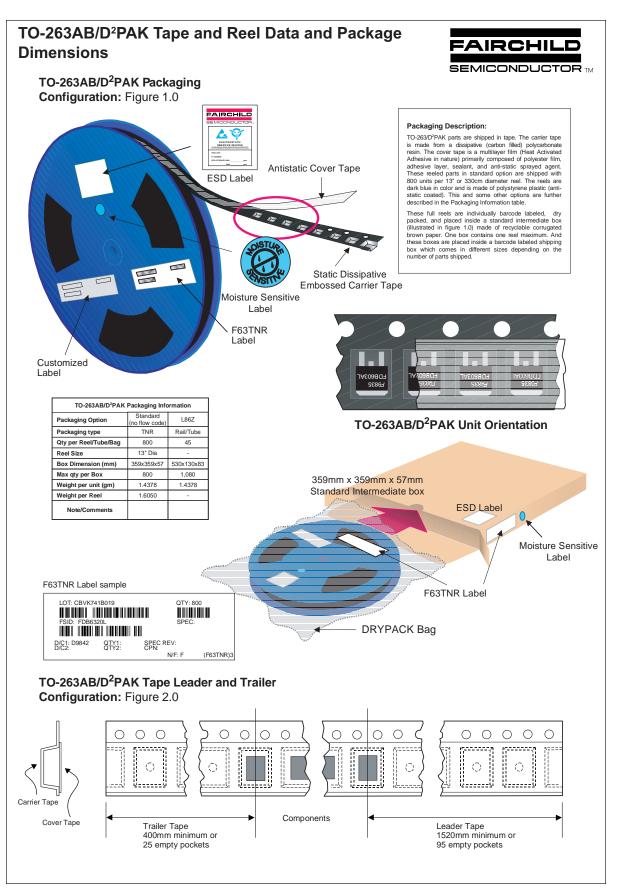




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

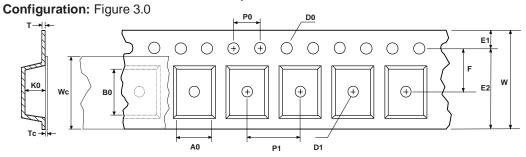
Part Weight per unit (gram): 1.4378





TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape



User Direction of Feed

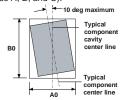
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D ² PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation

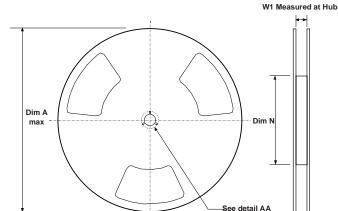


Sketch B (Top View)
Component Rotation

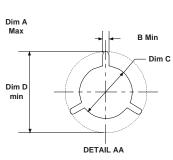


Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0



13" Diameter Option

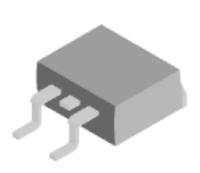


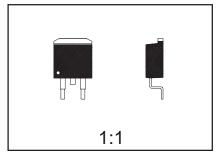
W2 max Measured at Hub

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

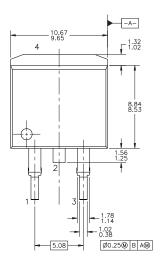
TO-263AB/D²PAK (FS PKG Code 45)

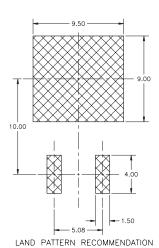


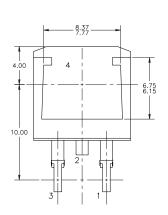


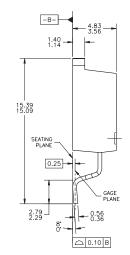
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
 E) REFERENCE JEDEC, TO—265, ISSUE C,
 VARIATION AB, DATED 2/92.

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Datasheet Identification	Product Status	Definition
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